

Vishay Siliconix

N-Channel 80 V (D-S) MOSFET



| PRODUCT SUMMARY | | | | | |
|--|--------------------|--|--|--|--|
| V _{DS} (V) | 80 | | | | |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$ | 0.034 | | | | |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = 7.5 \text{ V}$ | 0.044 | | | | |
| Q _g typ. (nC) | 7.1 | | | | |
| I _D (A) | 16 ^{a, g} | | | | |
| Configuration | Single | | | | |

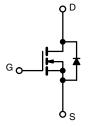
FEATURES

- TrenchFET® Gen IV power MOSFET
- Tuned for the lowest R_{DS} x Q_{oss} FOM
- 100 % Rq and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



APPLICATIONS

- Primary side switch
- DC/DC converter
- · Motor drive switch
- Boost converter
- LED backlighting



N-Channel MOSFET

| ORDERING INFORMATION | |
|---------------------------------|-----------------|
| Package | PowerPAK 1212-8 |
| Lead (Pb)-free and halogen-free | SiS108DN-T1-GE3 |

| ABSOLUTE MAXIMUM RATING | S (T _A = 25 °C, u | nless otherv | wise noted) | |
|--|-------------------------------------|-----------------------------------|---------------------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Drain-source voltage | | V_{DS} | 80 | V |
| Gate-source voltage | Gate-source voltage | | ± 20 | V |
| | T _C = 25 °C | | 16 ^a | |
| Continuous drain current (T _J = 150 °C) | T _C = 70 °C | Ι, | 14.7 | |
| | T _A = 25 °C | I _D | 6.7 b, c | |
| | T _A = 70 °C | | 5.4 b, c | ^ |
| Pulsed drain current (t = 100 μs) | | I _{DM} | 30 | A |
| Continuous source during displacement | T _C = 25 °C | | 16 ^a | |
| Continuous source-drain diode current | T _A = 25 °C | I _S | 2.6 ^{b, c} | |
| Single pulse avalanche current | L = 0.1 mH | I _{AS} | 12 | |
| Single pulse avalanche energy | L = 0.1 min | E _{AS} | 7.2 | mJ |
| | T _C = 25 °C | | 24 | |
| Maying may a dispination | T _C = 70 °C | | 15 | w |
| Maximum power dissipation | T _A = 25 °C | P _D | 3.2 b, c | VV |
| | T _A = 70 °C | ĺ | 2.1 ^{b, c} | |
| Operating junction and storage temperature range | | T _J , T _{stg} | -55 to +150 | °C |
| Soldering recommendations (peak temperature) d, e | | | 260 | |

| THERMAL RESISTANCE RATING | GS | | | | |
|----------------------------------|--------------|-------------------|---------|---------|------|
| PARAMETER | | SYMBOL | TYPICAL | MAXIMUM | UNIT |
| Maximum junction-to-ambient b, f | t ≤ 10 s | R _{thJA} | 31 | 39 | °C/W |
| Maximum junction-to-case (drain) | Steady state | R _{thJC} | 4.2 | 5.2 | C/VV |

Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 10 s
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 81 °C/W
- g. $T_C = 25$ °C

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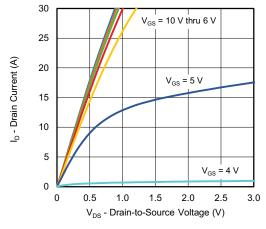
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--|-------------------------|---|---|-------|-------|-------|
| Static | | | | • | • | |
| Drain-source breakdown voltage | V_{DS} | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | 80 | - | - | V |
| V _{DS} temperature coefficient | $\Delta V_{DS}/T_{J}$ | I _D = 250 μA | - | 60 | - | |
| V _{GS(th)} temperature coefficient | $\Delta V_{GS(th)}/T_J$ | I _D = 250 μA | - | -6.8 | - | mV/°C |
| Gate-source threshold voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | 2 | - | 4 | V |
| Gate-source leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | - | - | 100 | nA |
| Zana mata walta na alumin ayumant | , | V _{DS} = 80 V, V _{GS} = 0 V | - | - | 1 | |
| Zero gate voltage drain current | I _{DSS} | V _{DS} = 80 V, V _{GS} = 0 V, T _J = 70 °C | - | - 10 | 10 | μA |
| On-state drain current ^a | I _{D(on)} | $V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$ | 10 | - | - | Α |
| Duning and the second of the s | Б | V _{GS} = 10 V, I _D = 4 A | - | 0.028 | 0.034 | |
| Drain-source on-state resistance a | R _{DS(on)} | V _{GS} = 7.5 V, I _D = 2 A | - | 0.031 | 0.044 | Ω |
| Forward transconductance a | 9 _{fs} | V _{DS} = 15 V, I _D = 15 A | - | 28 | - | S |
| Dynamic ^b | | | | • | • | |
| Input capacitance | C _{iss} | | - | 545 | - | |
| Output capacitance | C _{oss} | $V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | - | 75 | - | pF |
| Reverse transfer capacitance | C _{rss} | | - | 9 | - | |
| | | V _{DS} = 40 V, V _{GS} = 10 V, I _D = 4 A | ', V _{GS} = 10 V, I _D = 4 A - | | 13 | |
| Total gate charge | Qg | | - | 7.1 | 10 | |
| Gate-source charge | Q _{qs} | $V_{DS} = 40 \text{ V}, V_{GS} = 7.5 \text{ V}, I_D = 4 \text{ A}$ | - | 2.8 | - | nC |
| Gate-drain charge | Q _{gd} | | - | 1.7 | - | |
| Output charge | Q _{oss} | $V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$ | - | 9 | - | |
| Gate resistance | R _q | f = 1 MHz | 0.3 | 1.3 | 2.6 | Ω |
| Turn-on delay time | t _{d(on)} | | - | 10 | 20 | |
| Rise time | t _r | $V_{DD} = 40 \text{ V}, R_L = 10 \Omega, I_D \cong 4 \text{ A},$ | - | 5 | 10 | |
| Turn-off delay time | t _{d(off)} | $V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$ | - | 14 | 30 | 1 |
| Fall time | t _f | | - | 5 | 10 | |
| Turn-on delay time | t _{d(on)} | | - | 11 | 20 | ns |
| Rise time | t _r | $V_{DD} = 40 \text{ V}, R_{I} = 10 \Omega, I_{D} \cong 4 \text{ A},$ | - | 5 | 10 | |
| Turn-off delay time | t _{d(off)} | $V_{GEN} = 7.5 \text{ V}, R_g = 1 \Omega$ | - | 12 | 25 | |
| Fall time | t _f | | - | 5 | 10 | 1 |
| Drain-Source Body Diode Characteristi | cs | | | | | 1 |
| Continuous source-drain diode current | I _S | T _C = 25 °C | - | - | 16 | |
| Pulse diode forward current | I _{SM} | | - | - | 30 | A |
| Body diode voltage | V _{SD} | I _S = 4 A, V _{GS} = 0 V | - | 0.82 | 1.2 | V |
| Body diode reverse recovery time | t _{rr} | 2 00 | - | 30 | 60 | ns |
| Body diode reverse recovery charge | Q _{rr} | $I_F = 4 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$ | _ | 25 | 50 | nC |
| Reverse recovery fall time | t _a | $T_J = 25 ^{\circ}\text{C}$ | | 20 | - | † |
| Reverse recovery rise time | t _b | - | _ | 10 | _ | ns |

Notes

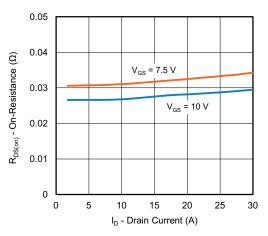
- a. Pulse test: pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

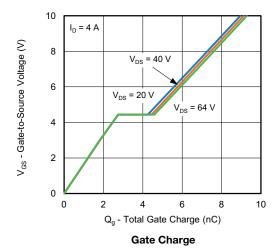


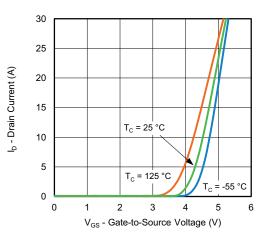


Output Characteristics

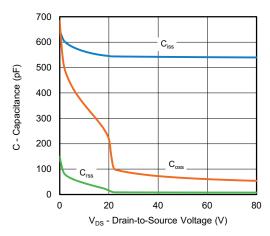


On-Resistance vs. Drain Current and Gate Voltage

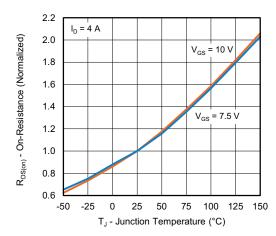




Transfer Characteristics

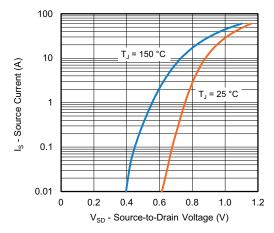


Capacitance

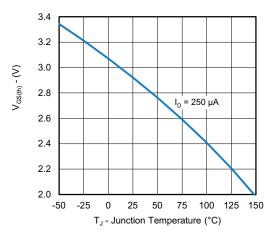


On-Resistance vs. Junction Temperature

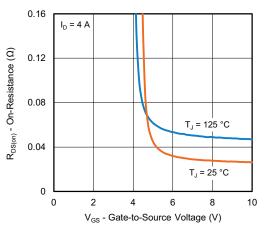




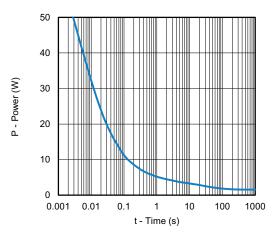
Source-Drain Diode Forward Voltage



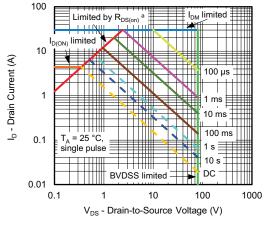
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

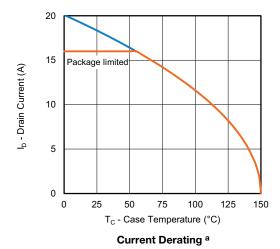


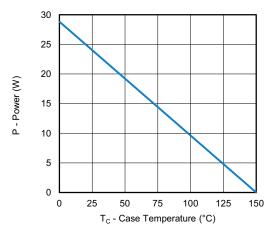
Safe Operating Area, Junction-to-Ambient

Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified





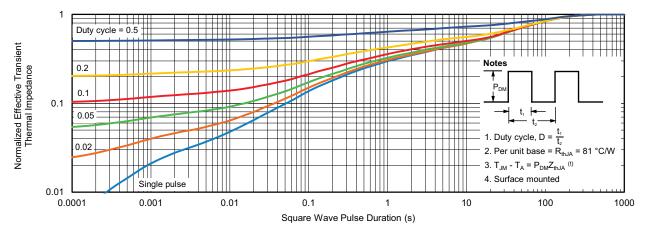


Power, Junction-to-Case

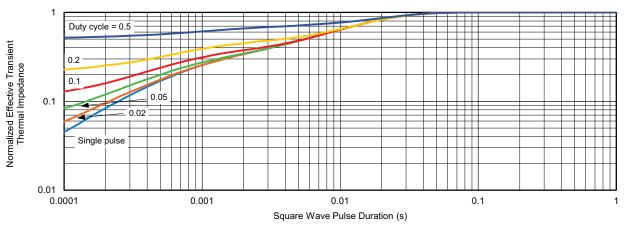
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient

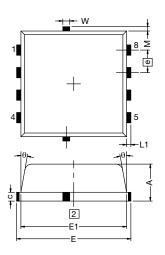


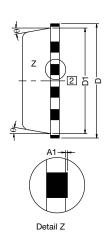
Normalized Thermal Transient Impedance, Junction-to-Case

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PowerPAK® 1212-8, (Single / Dual)

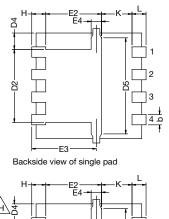


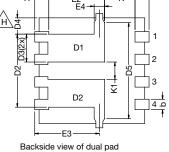


Notes

DWG: 5882

- 1. Inch will govern
- Dimensions exclusive of mold gate burrs
 Dimensions exclusive of mold flash and cutting burrs



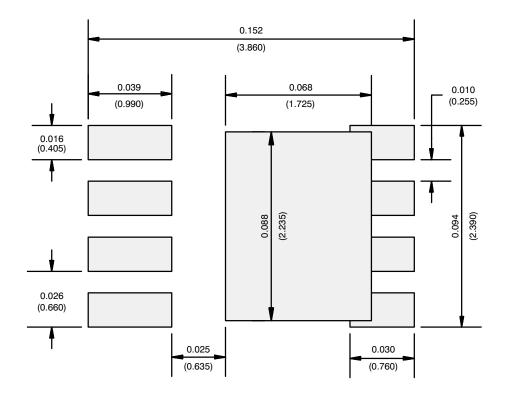


| DIM | MILLIMETERS | | | INCHES | | | |
|------|-------------|------------|------|------------|------------|-------|--|
| DIM. | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. | |
| Α | 0.97 | 1.04 | 1.12 | 0.038 | 0.041 | 0.044 | |
| A1 | 0.00 | = | 0.05 | 0.000 | - | 0.002 | |
| b | 0.23 | 0.30 | 0.41 | 0.009 | 0.012 | 0.016 | |
| С | 0.23 | 0.28 | 0.33 | 0.009 | 0.011 | 0.013 | |
| D | 3.20 | 3.30 | 3.40 | 0.126 | 0.130 | 0.134 | |
| D1 | 2.95 | 3.05 | 3.15 | 0.116 | 0.120 | 0.124 | |
| D2 | 1.98 | 2.11 | 2.24 | 0.078 | 0.083 | 0.088 | |
| D3 | 0.48 | - | 0.89 | 0.019 | - | 0.035 | |
| D4 | | 0.47 typ. | | | 0.0185 typ | | |
| D5 | | 2.3 typ. | | 0.090 typ | | | |
| E | 3.20 | 3.30 | 3.40 | 0.126 | 0.130 | 0.134 | |
| E1 | 2.95 | 3.05 | 3.15 | 0.116 | 0.120 | 0.124 | |
| E2 | 1.47 | 1.60 | 1.73 | 0.058 | 0.063 | 0.068 | |
| E3 | 1.75 | 1.85 | 1.98 | 0.069 | 0.073 | 0.078 | |
| E4 | | 0.034 typ. | | 0.013 typ. | | | |
| е | | 0.65 BSC | | 0.026 BSC | | | |
| K | | 0.86 typ. | | 0.034 typ. | | | |
| K1 | 0.35 | - | - | 0.014 | - | - | |
| Н | 0.30 | 0.41 | 0.51 | 0.012 | 0.016 | 0.020 | |
| L | 0.30 | 0.43 | 0.56 | 0.012 | 0.017 | 0.022 | |
| L1 | 0.06 | 0.13 | 0.20 | 0.002 | 0.005 | 0.008 | |
| θ | 0° | - | 12° | 0° | - | 12° | |
| W | 0.15 | 0.25 | 0.36 | 0.006 | 0.010 | 0.014 | |
| М | 0.125 typ. | | | | 0.005 typ. | | |

Revison: 09-Jan-17 Document Number: 71656



RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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